AMENDMENTS TO THE CLAIMS

The following listing of claims replaces all prior versions of claims in the application.

1. (Previously presented): A substrate having organic thin film, characterized in that: a buffer layer and organic thin film are sequentially deposited on a substrate, and said buffer layer accelerates two dimensional growth of said organic thin film, and orients said organic thin film flatly.

2. (Original): The substrate having organic thin film as set forth in claim 1, characterized in that a layer easily oriented with said buffer layer is further inserted between said substrate and said buffer layer.

3. (Original): The substrate having organic thin film as set forth in claim 1, characterized in that said substrate is an insulating substrate, said buffer layer is acene system aromatics or its derivative, said organic thin film is either C_n fullerene (where n is an integer of 60 or more), C_n fullerene derivative, or rubrene.

4. (Original): The substrate having organic thin film as set forth in claim 3, characterized in that said insulating substrate is a sapphire substrate, said acene system aromatics is either pentacene or pentacene fluoride, and said C_n fullerene is C_{60}.

5. (Original): The substrate having organic thin film as set forth in claim 4, characterized in that the surface of said sapphire substrate is flattening-treated, and said buffer layer consisting of either pentacene or pentacene fluoride is deposited by molecular layer unit.

6. (Previously presented): A transistor provided with organic thin film formed on a substrate, characterized in that: said organic thin film is deposited on said substrate via the buffer layer accelerating two dimensional growth of said organic thin film, and orienting said organic thin film flatly.

7. (Original): The transistor as set forth in claim 6, characterized in that a layer easily oriented with said buffer layer is further inserted between said substrate and said buffer layer.

8. (Original): The transistor as set forth in claim 6, characterized in that said substrate is an insulating substrate, said buffer layer is acene system aromatics or its derivative, said organic thin film is either C_n fullerene (where n is an integer of 60 or more), C_n fullerene derivative, or rubrene.

9. (Original): The transistor as set forth in claim 8, characterized in that said insulating substrate is a sapphire substrate, said acene system aromatics is either pentacene or pentacene fluoride, and said C_n fullerene is C_{60}.

10. (Original): The transistor as set forth in claim 9, characterized in that the surface of said sapphire substrate is flattening-treated, and said buffer layer consisting of either pentacene or pentacene fluoride is deposited by molecular layer unit.

11. (Previously presented): A method of manufacturing a substrate having organic thin film, characterized in that: it includes a process of sequentially depositing a buffer layer and organic thin film on a substrate, and said buffer layer accelerates two dimensional growth of said organic thin film, and orients said organic thin film flatly.

12. (Original): The method of manufacturing a substrate having organic thin film as set forth in claim 11, characterized in that a layer easily oriented with said buffer layer is further inserted between said substrate and said buffer layer.

13. (Original): The method of manufacturing a substrate having organic thin film as set forth in claim 11, characterized in that said substrate is an insulating substrate, said buffer layer is

acene system aromatics or its derivative, said organic thin film is either C_n fullerene (where n is an integer of 60 or more), C_n fullerene derivative, or rubrene.

14. (Original): The method of manufacturing a substrate having organic thin film as set forth in claim 13, characterized in that said insulating substrate is a sapphire substrate, said acene system aromatics is either pentacene or pentacene fluoride, and said C_n fullerene is C_{60}.

15. (Original): The method of manufacturing a substrate having organic thin film as set forth in claim 14, characterized in that the surface of said sapphire substrate is flattening-treated, and said buffer layer consisting of either pentacene or pentacene fluoride is deposited by molecular layer unit.

16. (Previously presented): A method of manufacturing a transistor provided with organic thin film formed on a substrate, characterized in that: said organic thin film is deposited on said substrate via the buffer layer accelerating two dimensional growth of said organic thin film, and orienting said organic thin film flatly.

17. (Original): The method of manufacturing a transistor as set forth in claim 16, characterized in that a layer easily oriented with said buffer layer is further inserted between said substrate and said buffer layer.

18. (Original): The method of manufacturing a transistor as set forth in claim 16, characterized in that said substrate is an insulating substrate, said buffer layer is acene system aromatics or its derivative, said organic thin film is either C_n fullerene (where n is an integer of 60 or more), C_n fullerene derivative, or rubrene.

19. (Original): The method of manufacturing a transistor as set forth in claim 18, characterized in that said insulating substrate is a sapphire substrate, said acene system aromatics is either pentacene or pentacene fluoride, and said C_n fullerene is C_{60}.

20. (Original): The method of manufacturing a transistor as set forth in claim 19, characterized in that the surface of said sapphire substrate is flattening-treated, and said buffer layer consisting of either pentacene or pentacene fluoride is deposited by molecular layer unit.

21. (Previously presented): A substrate having organic thin film, characterized in that: a buffer layer and organic thin film are sequentially deposited on the substrate, said buffer layer is acene system aromatics or its derivative, said buffer layer accelerates two dimensional growth of said organic thin film, and orients said organic thin film flatly.

22. (Previously presented): A substrate having organic thin film, characterized in that: a buffer layer and organic thin film are sequentially deposited on the substrate, said buffer layer is acene system aromatics or its derivative, said organic thin film is either C_n fullerene (where n is an integer of 60 or more), C_n fullerene derivative, or rubrene, said buffer layer accelerates two dimensional growth of said organic thin film, and orients said organic thin film flatly.

23. (Previously presented): A transistor, characterized in that: it is a transistor having organic thin film formed on a substrate, said organic thin film is deposited on said substrate via a buffer layer consisting of acene system aromatics or its derivative, accelerating two dimensional growth of said organic thin film, and orienting the organic thin film flatly.

24. (Previously presented): A transistor, characterized in that: it is a transistor having organic thin film formed on a substrate, said organic thin film is deposited on said substrate via a buffer layer consisting of acene system aromatics or its derivative, accelerating two dimensional

growth of said organic thin film, and orienting the organic thin film flatly, and said organic thin film is either C_n fullerene (where n is an integer of 60 or more), C_n fullerene derivative, or rubrene.